

GSC4762

NPN EPITAXIAL SILICON TRANSISTOR

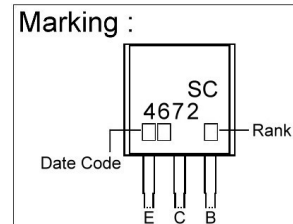
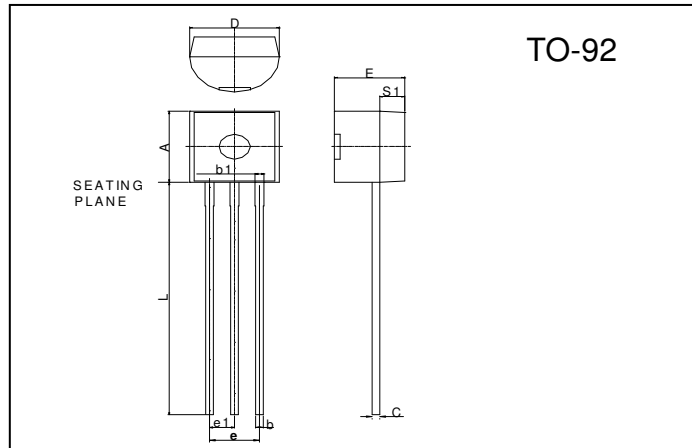
Description

The GSC4672 is designed for low frequency amplifier applications.

Features

- Low saturation voltage, typically $V_{CE(sat)} = 0.1V$ at $I_C/I_B = 1A/50mA$
- Excellent DC current gain characteristics

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings ($T_A = 25^\circ C$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	2	A
Collector Current (Pulse PW=10ms)	I_C	5	A
Total Device Dissipation	P_D	750	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ C$

Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

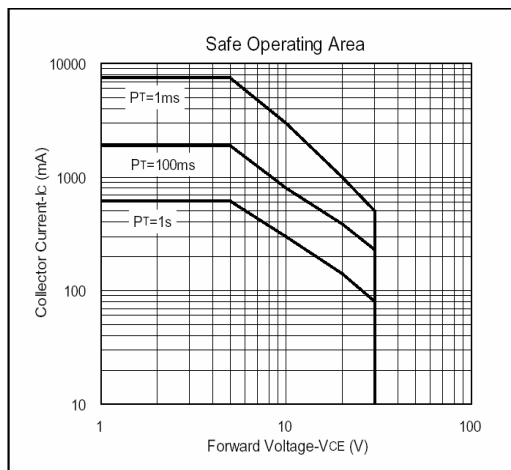
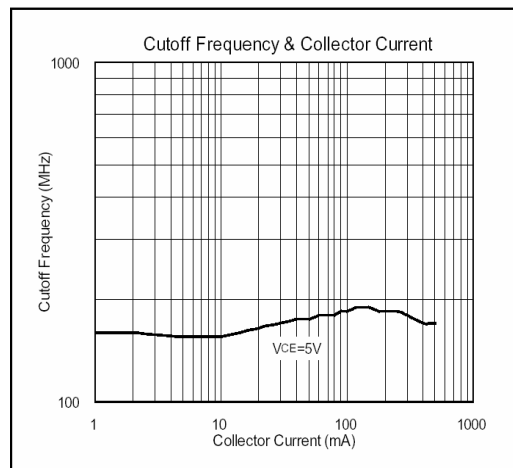
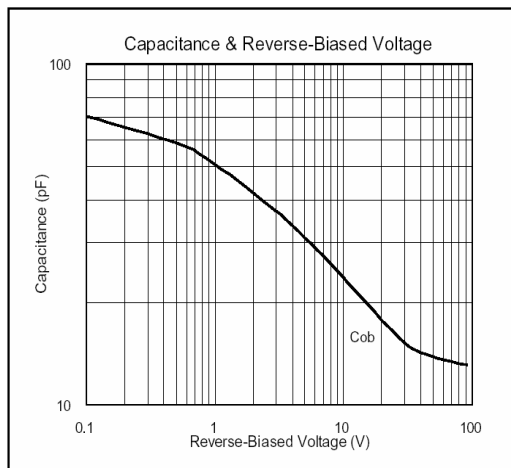
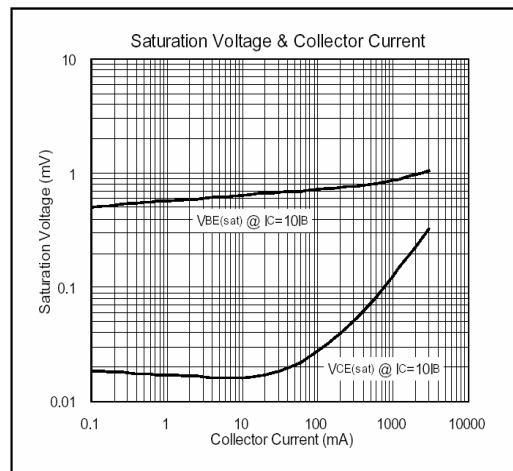
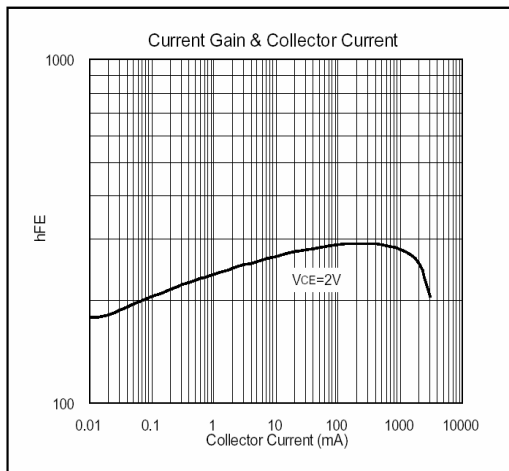
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	60	-	-	V	$I_C = 50\mu A, I_E = 0$
BV_{CEO}	50	-	-	V	$I_C = 1mA, I_B = 0$
BV_{EBO}	6	-	-	V	$I_E = 50\mu A, I_C = 0$
I_{CBO}	-	-	100	nA	$V_{CB} = 60V, I_E = 0$
I_{EBO}	-	-	100	nA	$V_{EB} = 5V, I_C = 0$
$*V_{CE(sat)}$	-	0.1	0.35	V	$I_C = 1A, I_B = 50mA$
$*h_{FE}$	120	-	400		$V_{CE} = 2V, I_C = 500mA$
fT	-	210	-	MHz	$V_{CE} = 2V, I_E = 500mA, f = 100MHz$
Cob	-	25	-	pF	$V_{CB} = 10V, I_E = 0, f = 1MHz$

*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE}

Rank	A	B
Range	120 ~ 240	200 ~ 400

Characteristics Curve



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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165